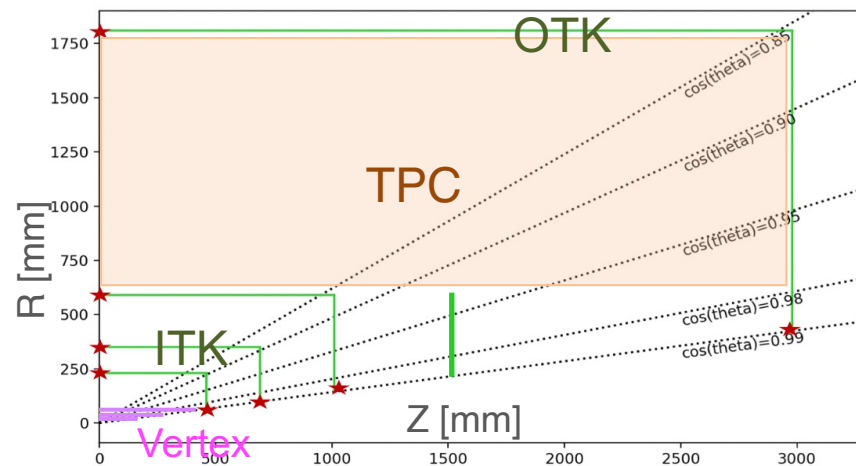


Tracker ITK TDR 的工作进度报告（3）

严琪

2024年7月26日

Tracker探测器Baseline不同层的排布



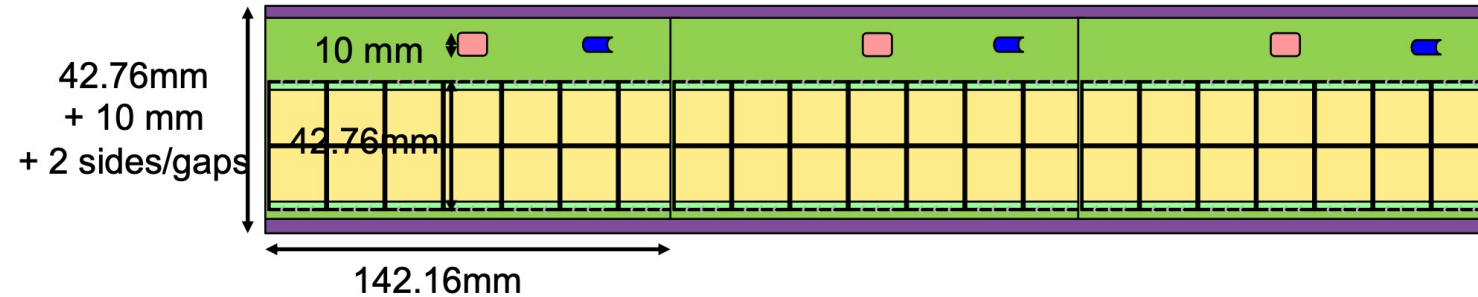
端盖	ITKE1	ITKE2	ITKE3	ITKE4	OTKE
Z [mm]	500.5	715	1001	1500	2903
R-I [mm]	75	101.9	142.6	214	405.7
R-O[mm]	240	350	600	600	1801

桶部	VTX1	VTX2	VTX3	VTX4	VTX5	VTX6	ITKB1	ITKB2	ITKB3	OTKB
R [mm]	12.46		27.89		43.79		240	350	600	1800
Half-Z [mm]	130	130	247	247	374.5	374.5	500.5	715	1001	2900

李刚、严琪

桶部Sensor、Module、和Stave模块的旧方案

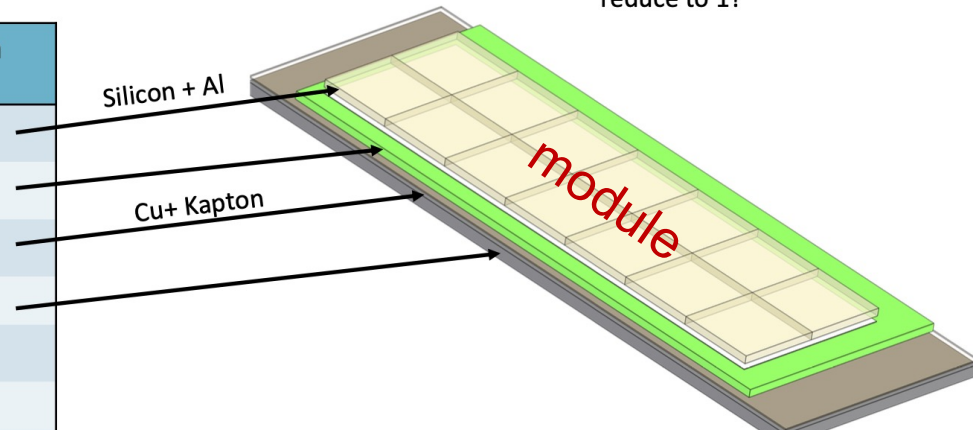
stave



IpGBTx: W=9, L=9
Optical connector: W=10, L=20

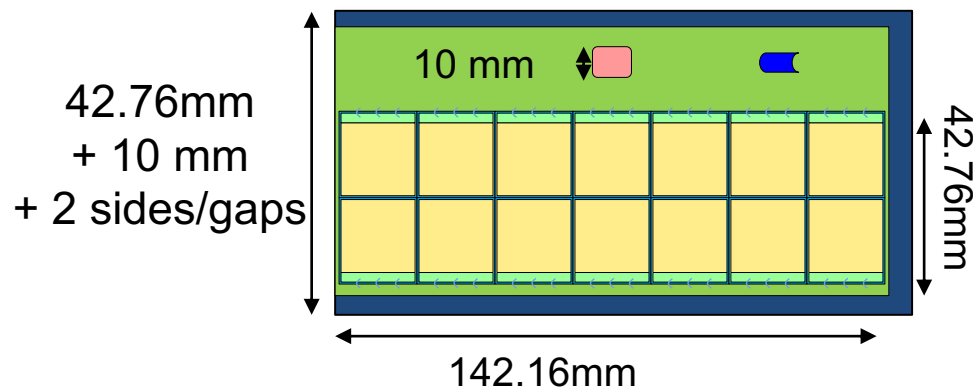
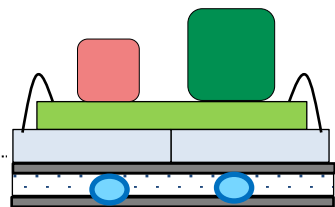
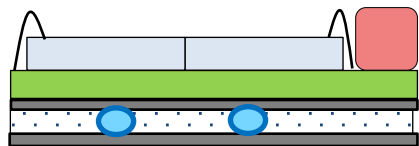
1 IpGBT provides 28×0.32,
14×0.64, or 7×1.28 Gbps
DATA links
=> 2 IpGBT needed for
current bkg rate; may
reduce to 1?

	Thickness (mm)	Radiation Length [%X0]
Pixel Sensor	0.150	0.18
HybridFlex	0.200	0.28
Kapton Tape	0.100	0.14
BareStave	4.000	0.21
Optical connector	1.250	0.13
IpGBTx	4.000	0.07

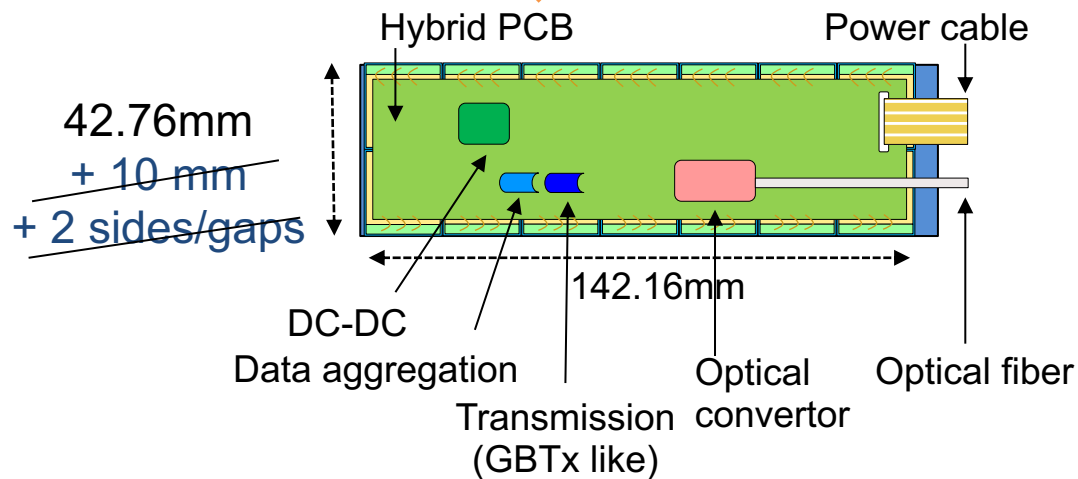


李一鸣(2024.07.10) @ ITK+OTK meeting

桶部Module的最新方案



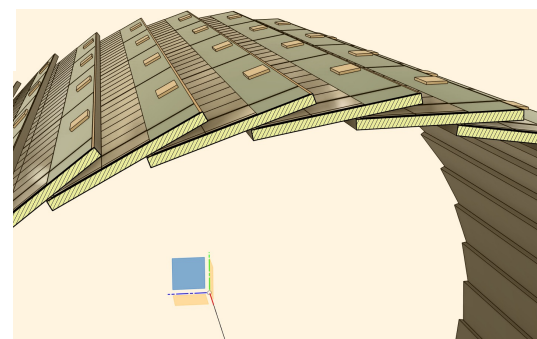
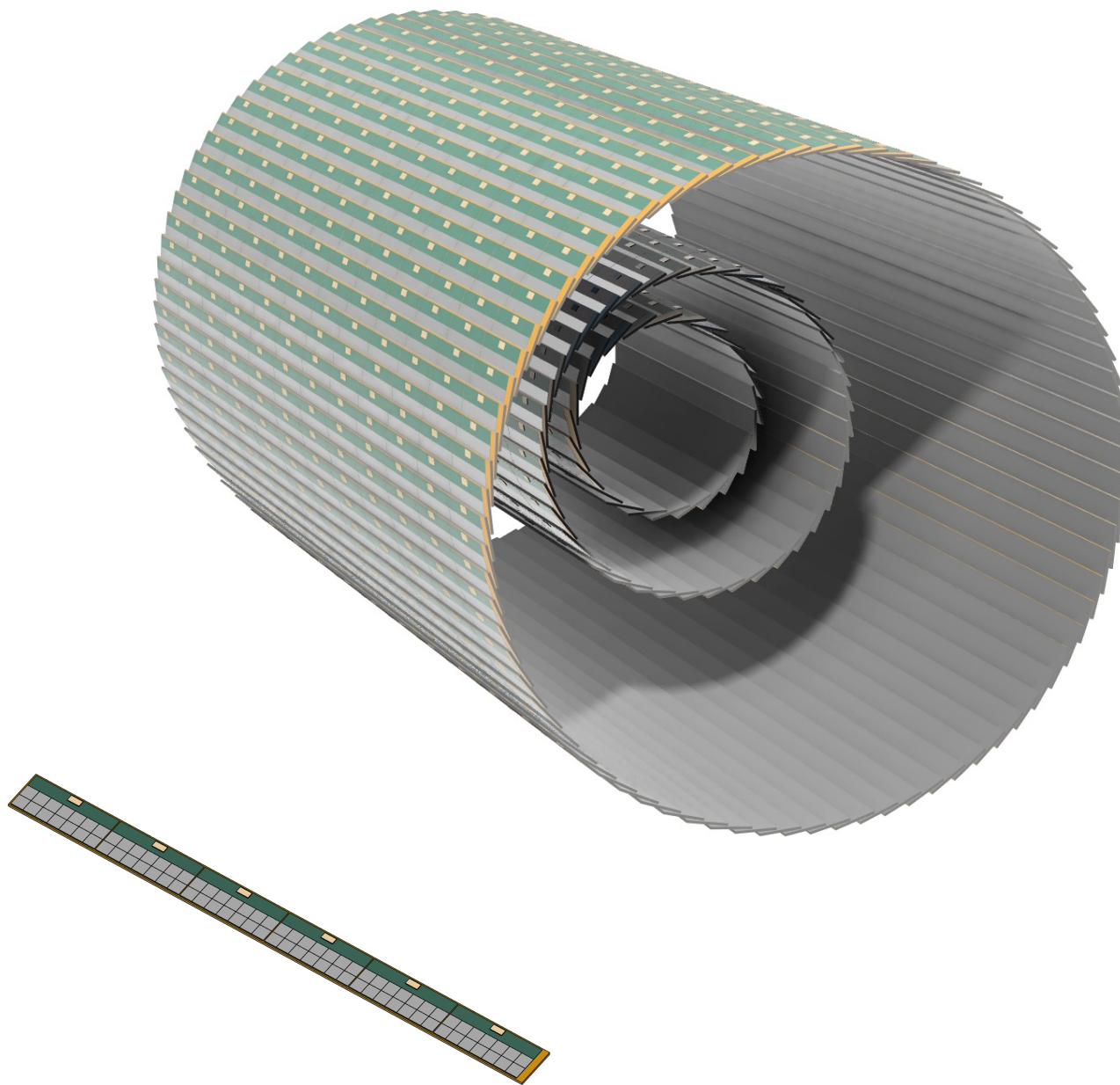
李一鸣(2024.07.23) et al. 最新更新



新方案提高了探测效率，并有助于优化散热和机械结构的设计。

桶部排布的3维几何排布（旧图需要更新）

严琪、张奕晗



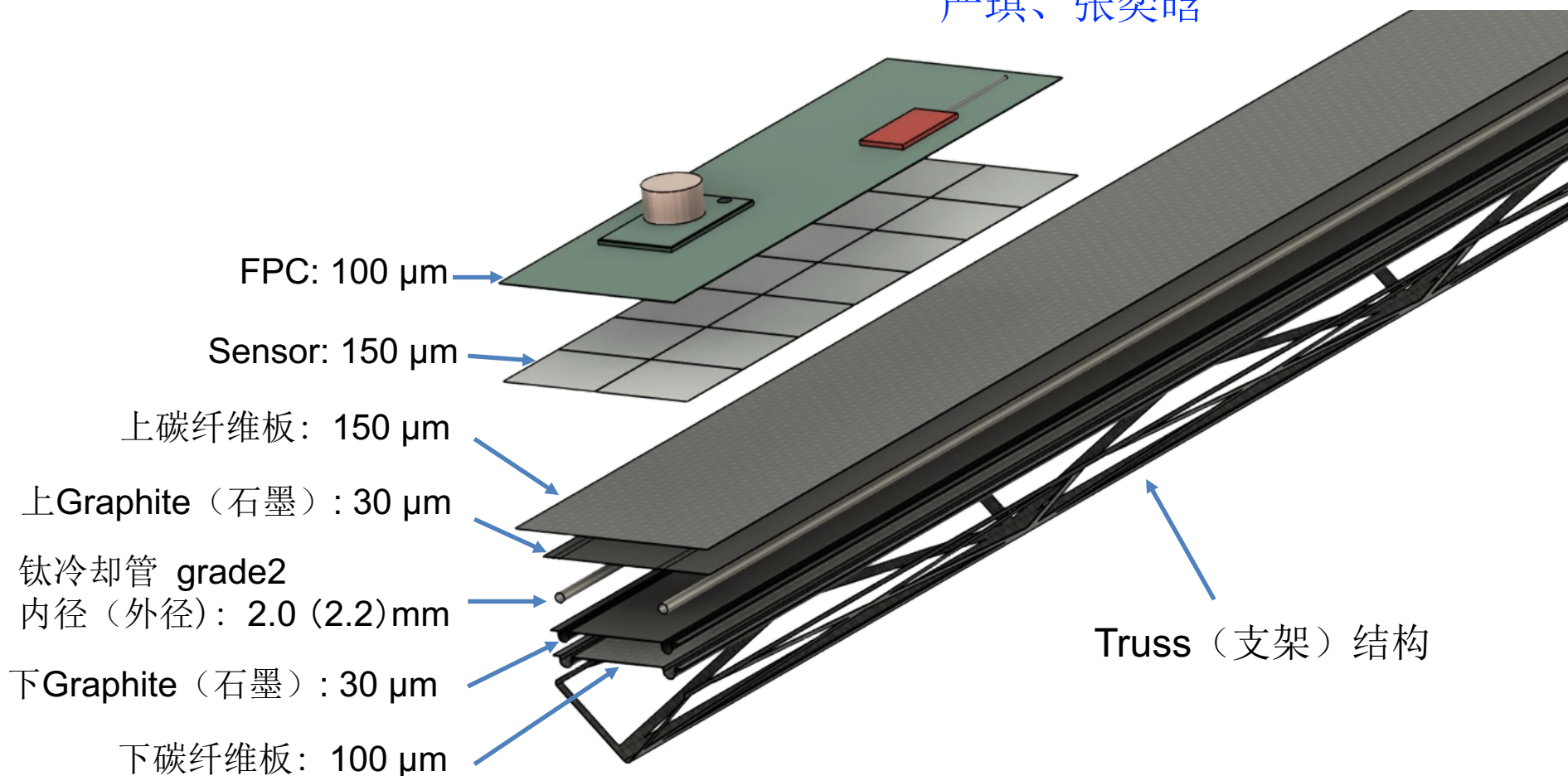
桶部探测元件统计

	Modules/Stave	Staves	Modules	Sensors	Sensor area
ITKB1	7	40	280	3920	1.6 m ²
ITKB2	10	58	580	8120	3.2 m ²
ITKB3	14	96	1344	18816	7.5 m ²
Total		194	2204	30856	12.3 m ²

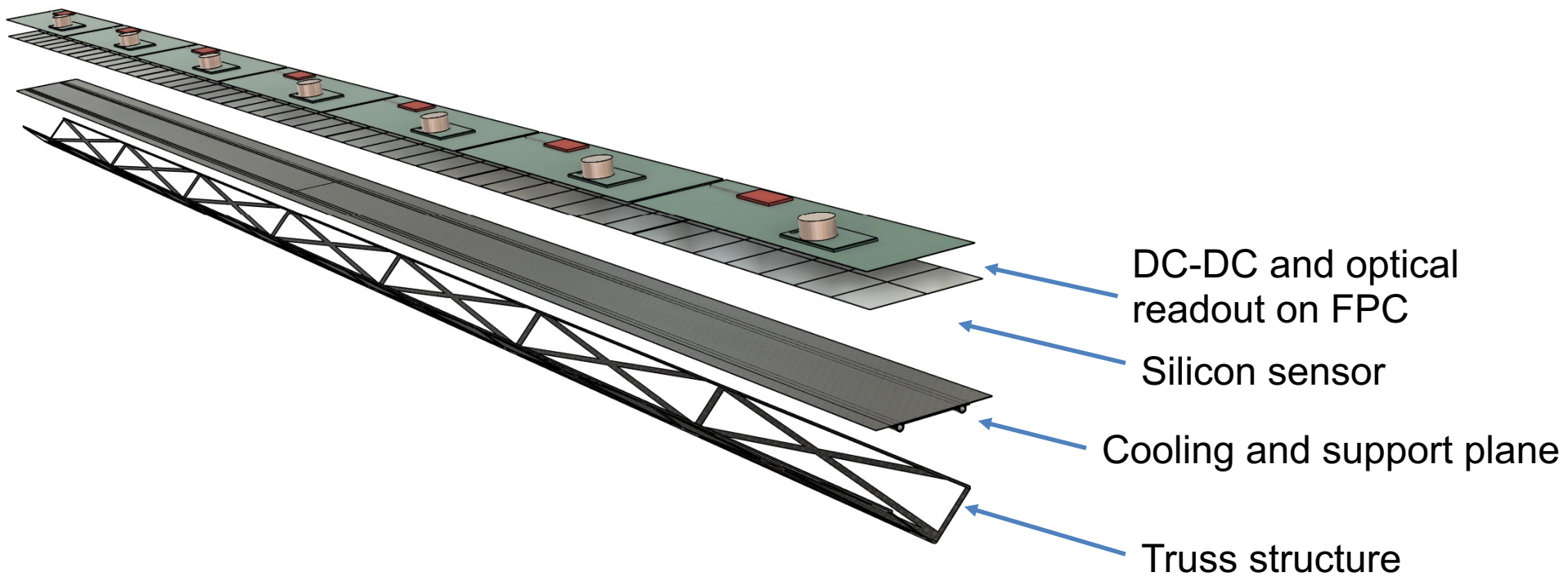
芯片的总功耗（不包括其他电子学元件）： 24.6 KW (200 mW/cm²)

桶部Stave的机械和散热设计和分析

严琪、张奕晗

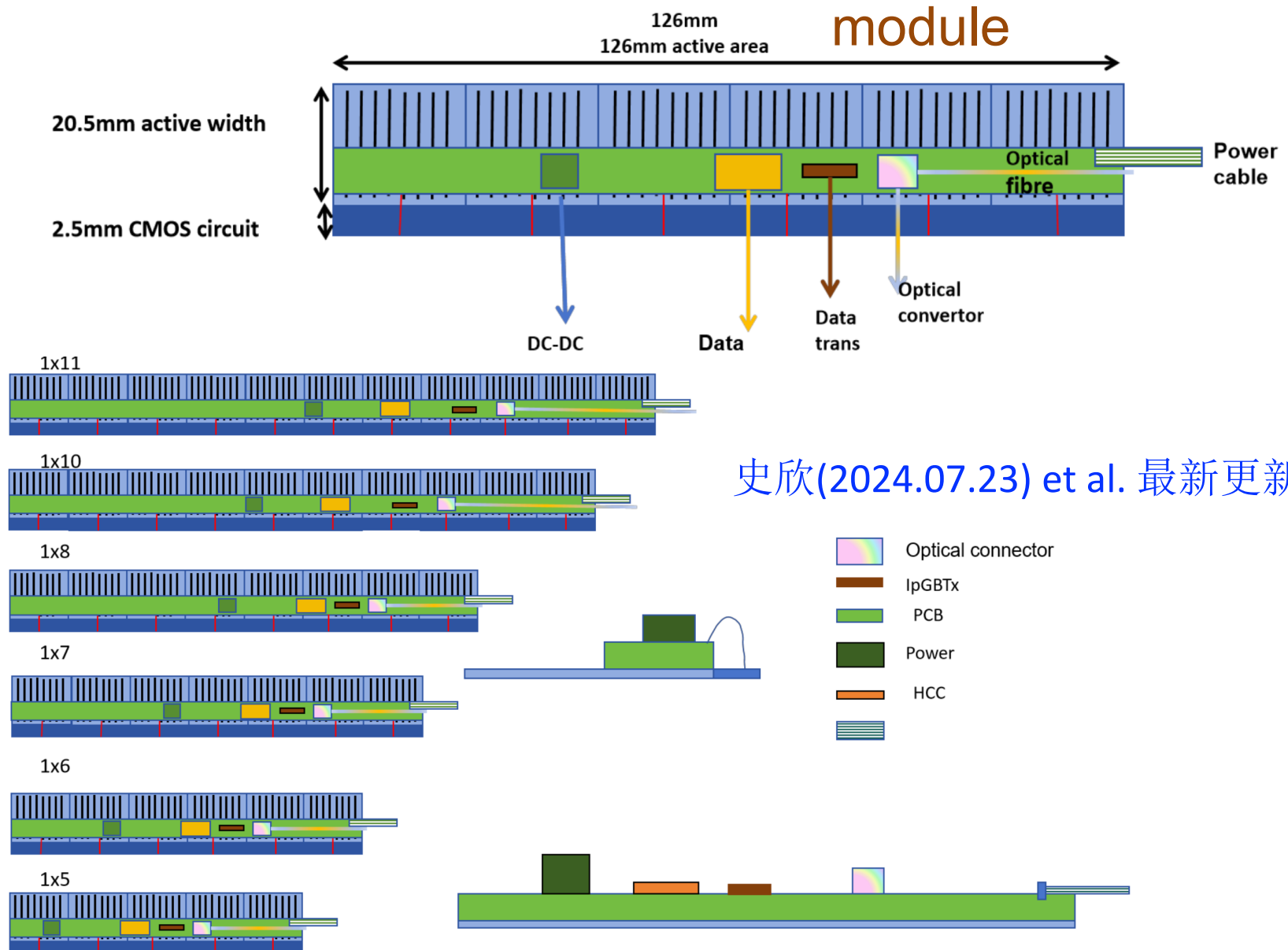


严琪、张奕晗



机械和热分析的工作还在进行中.....

端盖Sensor和Module的方案



史欣(2024.07.23) et al. 最新更新

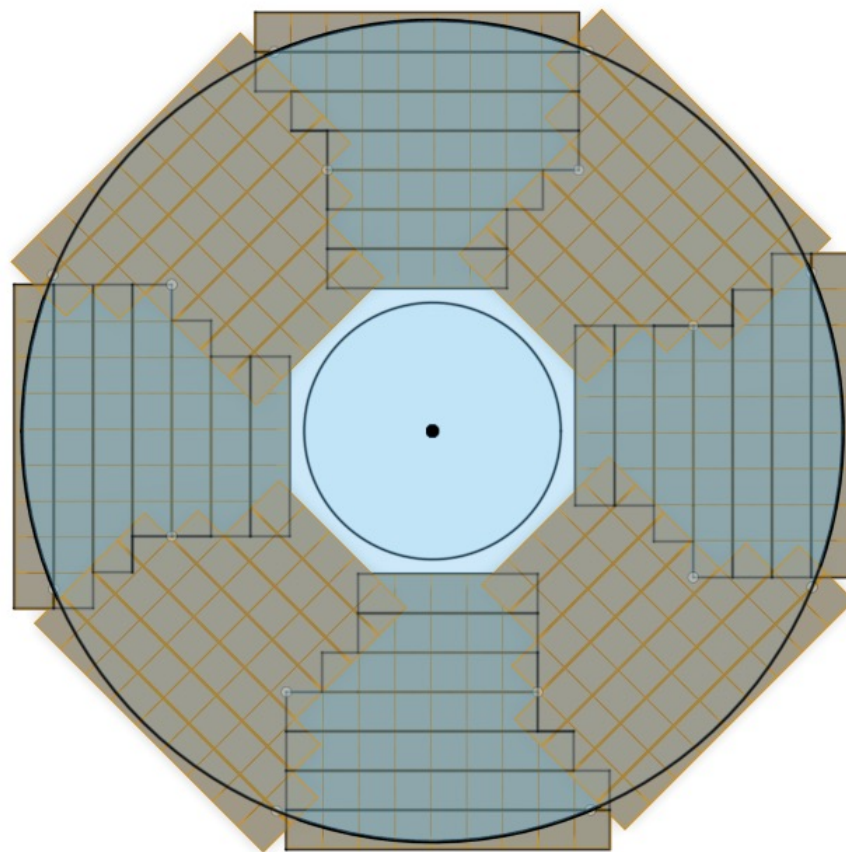
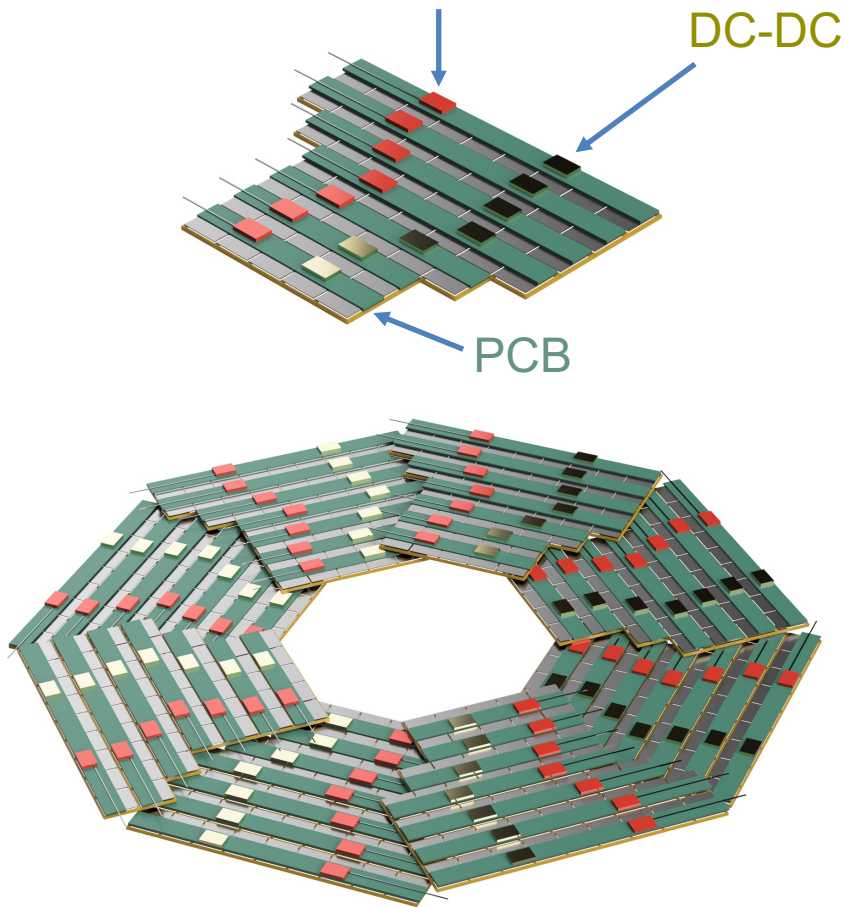
端盖的最新排布方案（第一个端盖ITKE1）

严琪、骆首栋、史欣

Optical convertor

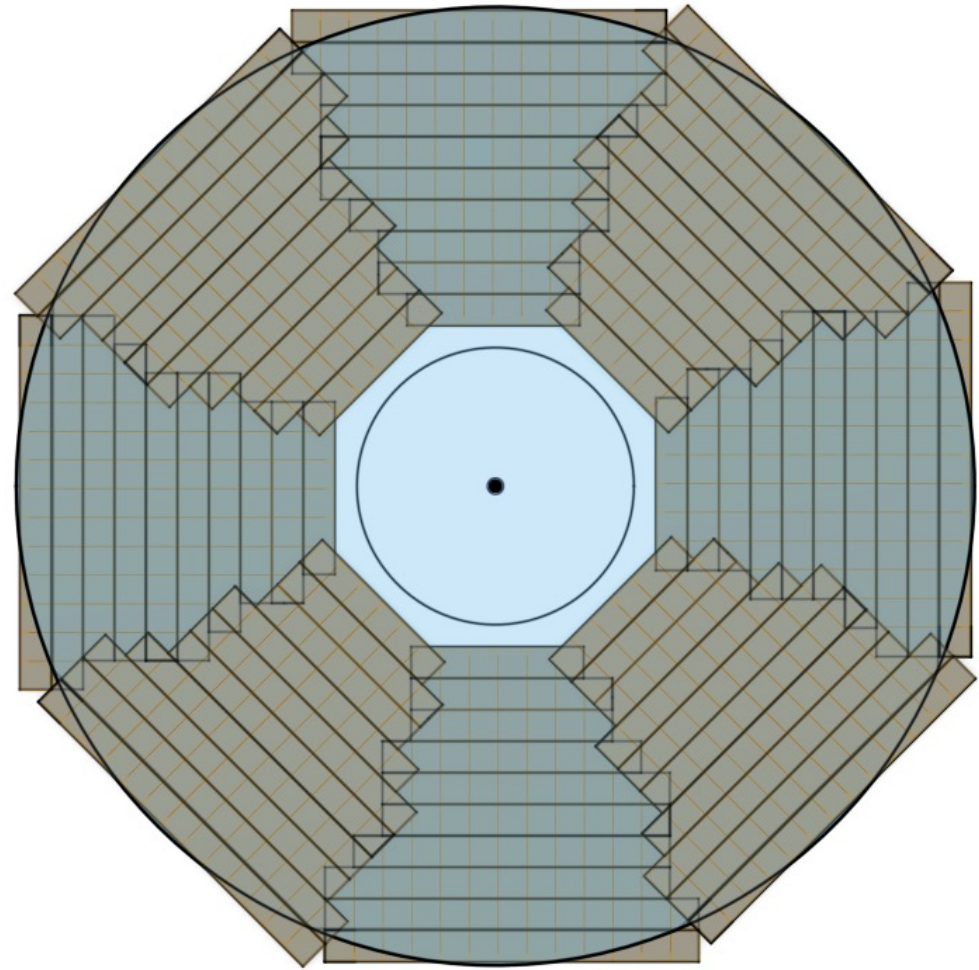
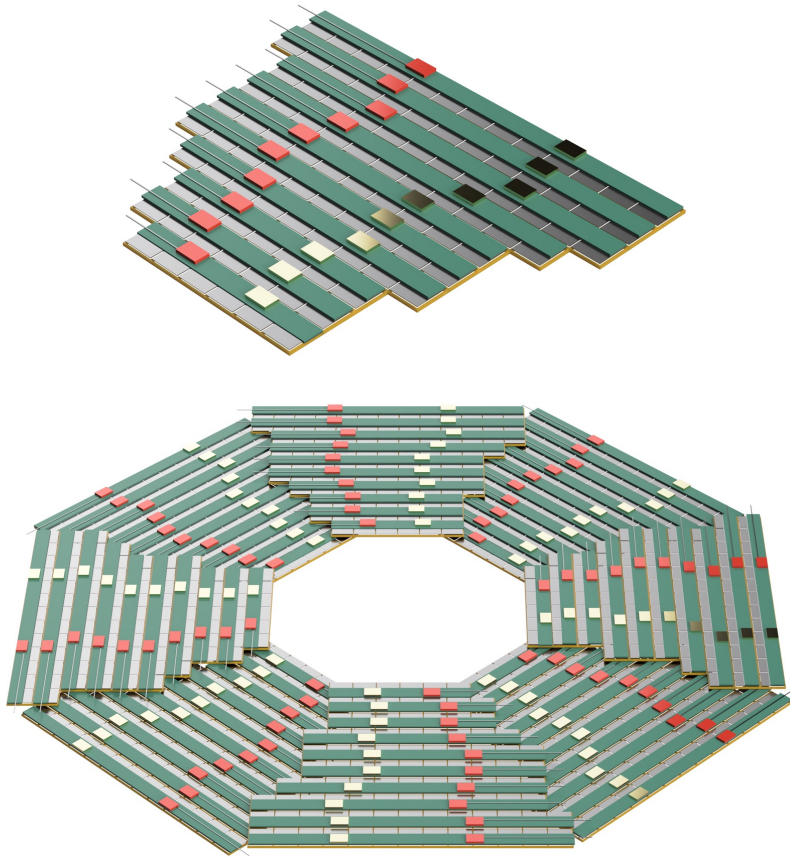
DC-DC

PCB



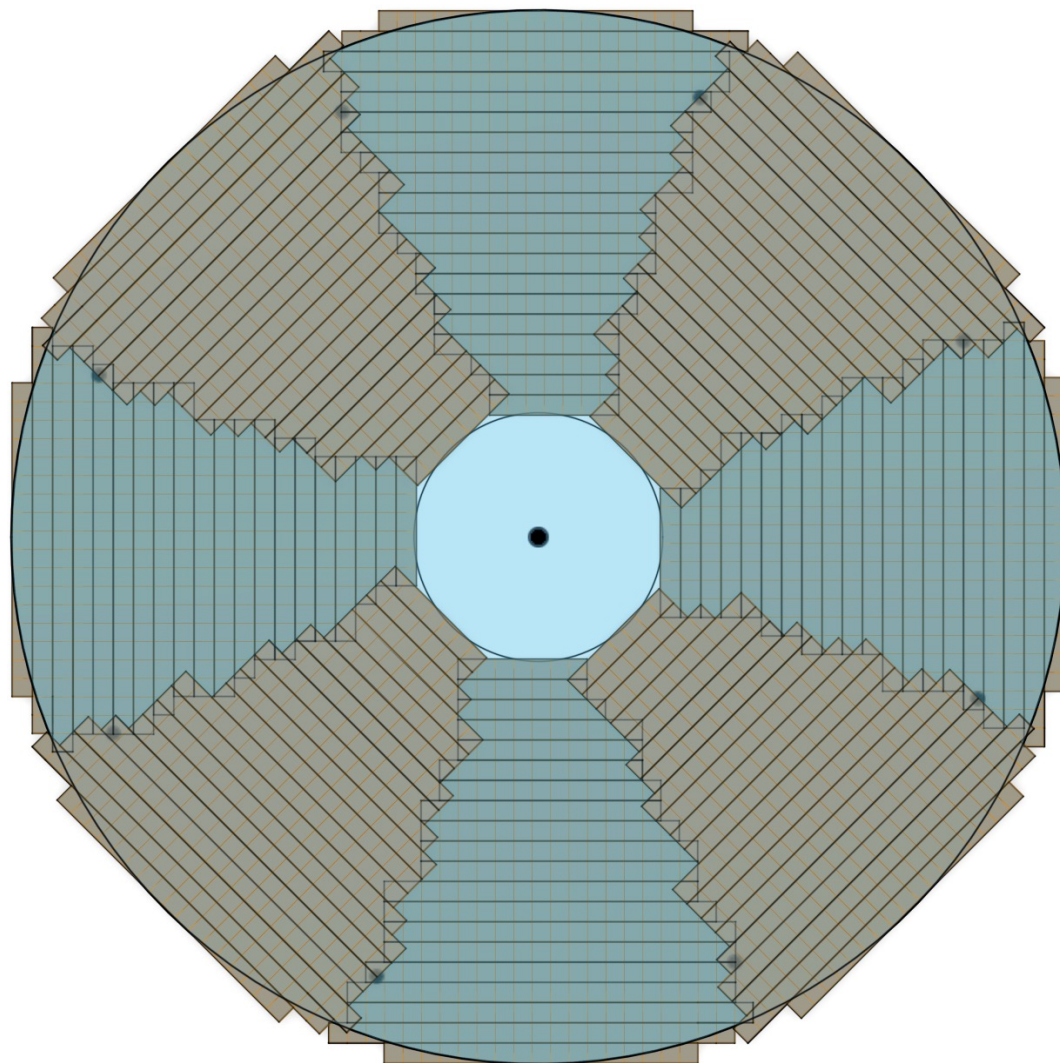
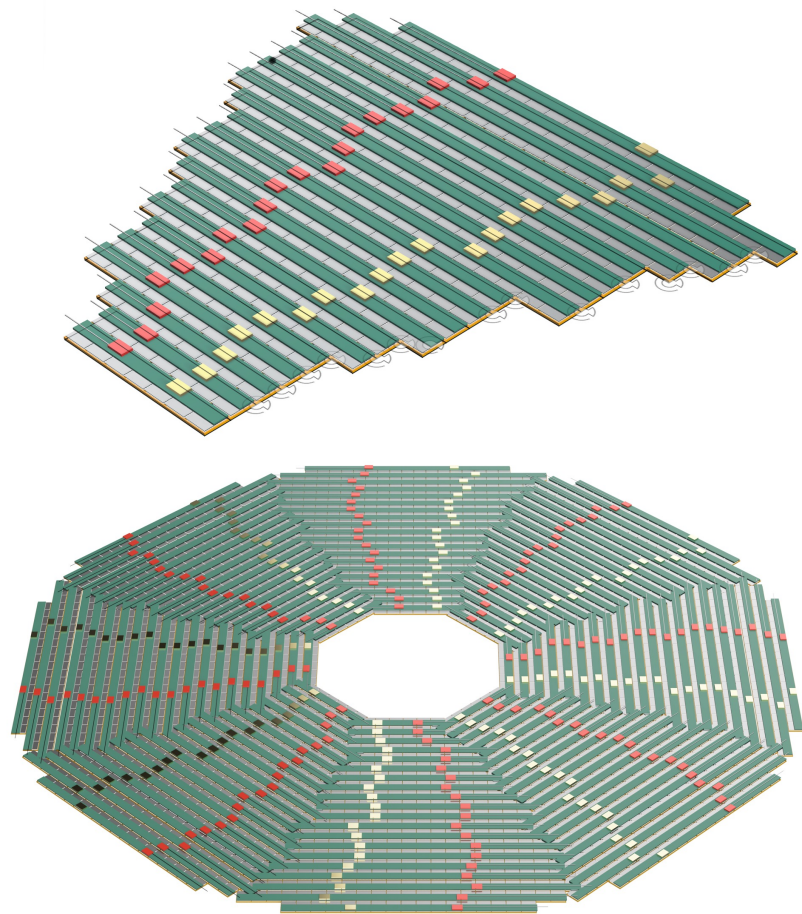
端盖的最新排布方案（第二个端盖ITKE2）

严琪、骆首栋、史欣



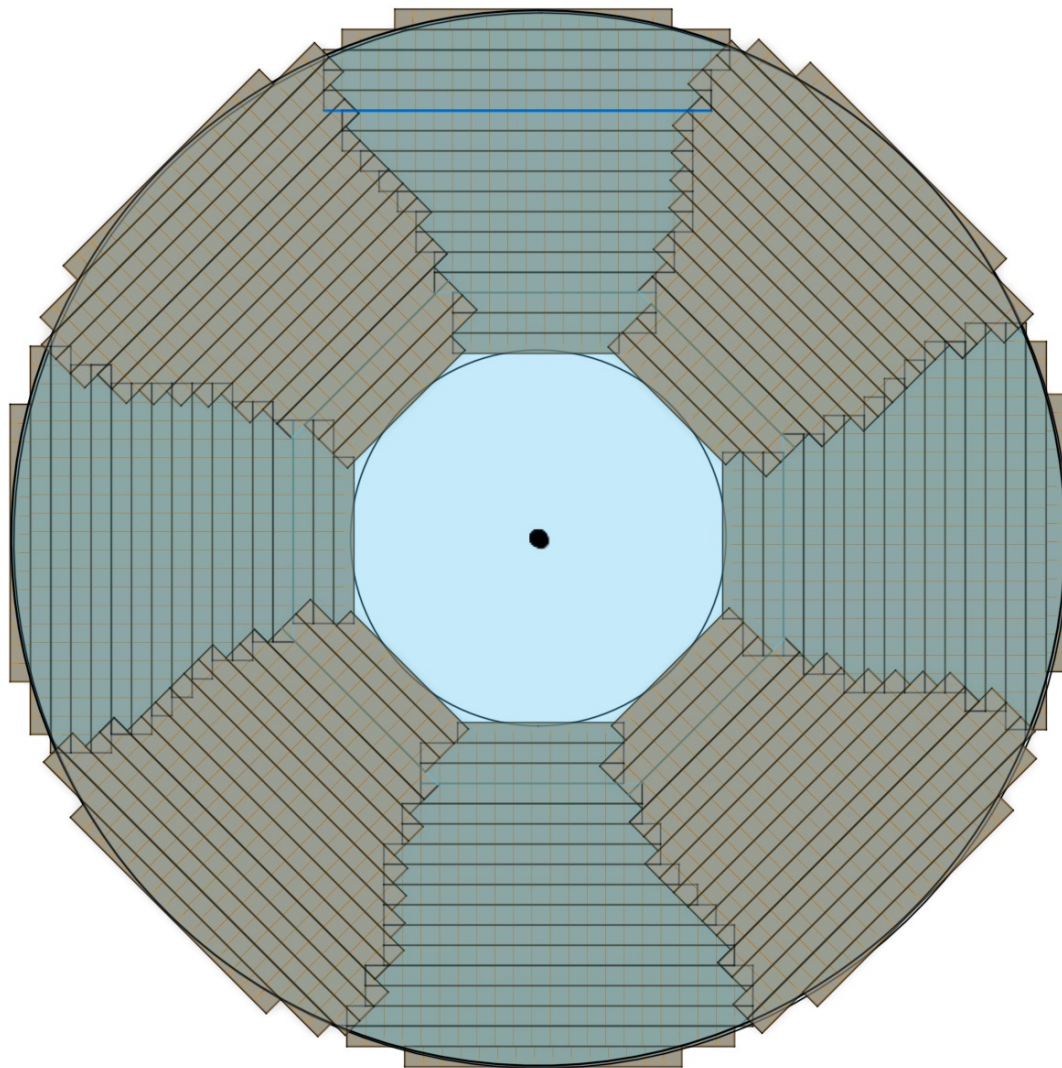
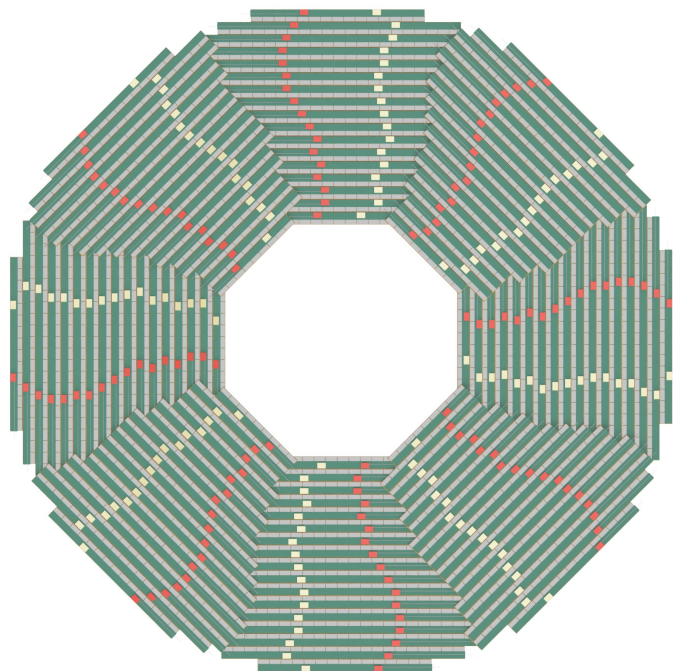
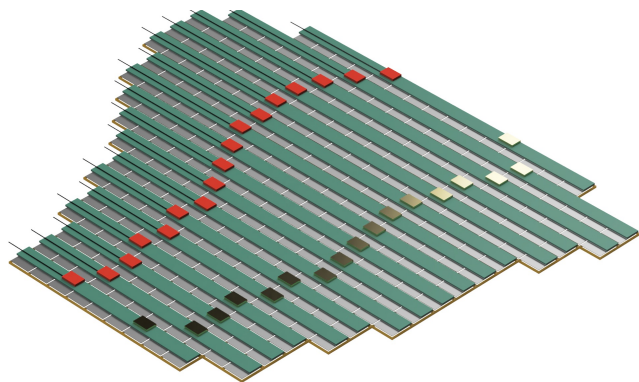
端盖的最新排布方案（第三个端盖ITKE3）

严琪、骆首栋、史欣



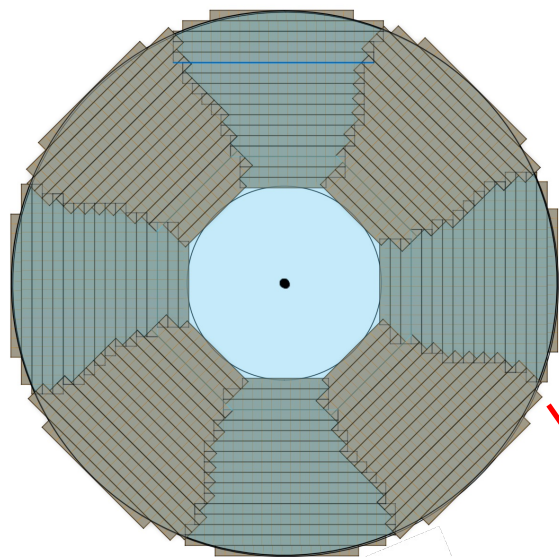
端盖的最新排布方案（第四个端盖ITKE4）

严琪、骆首栋、史欣

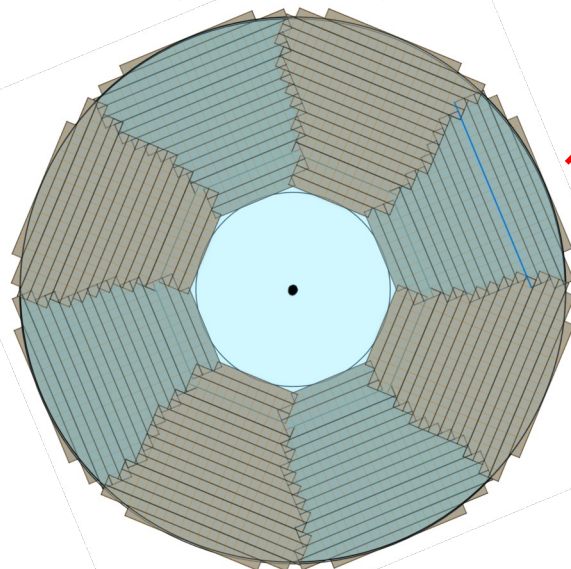


单面Strip Detector端盖的最新排布方案

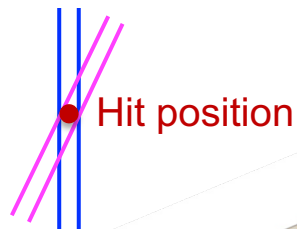
严琪、骆首栋、史欣



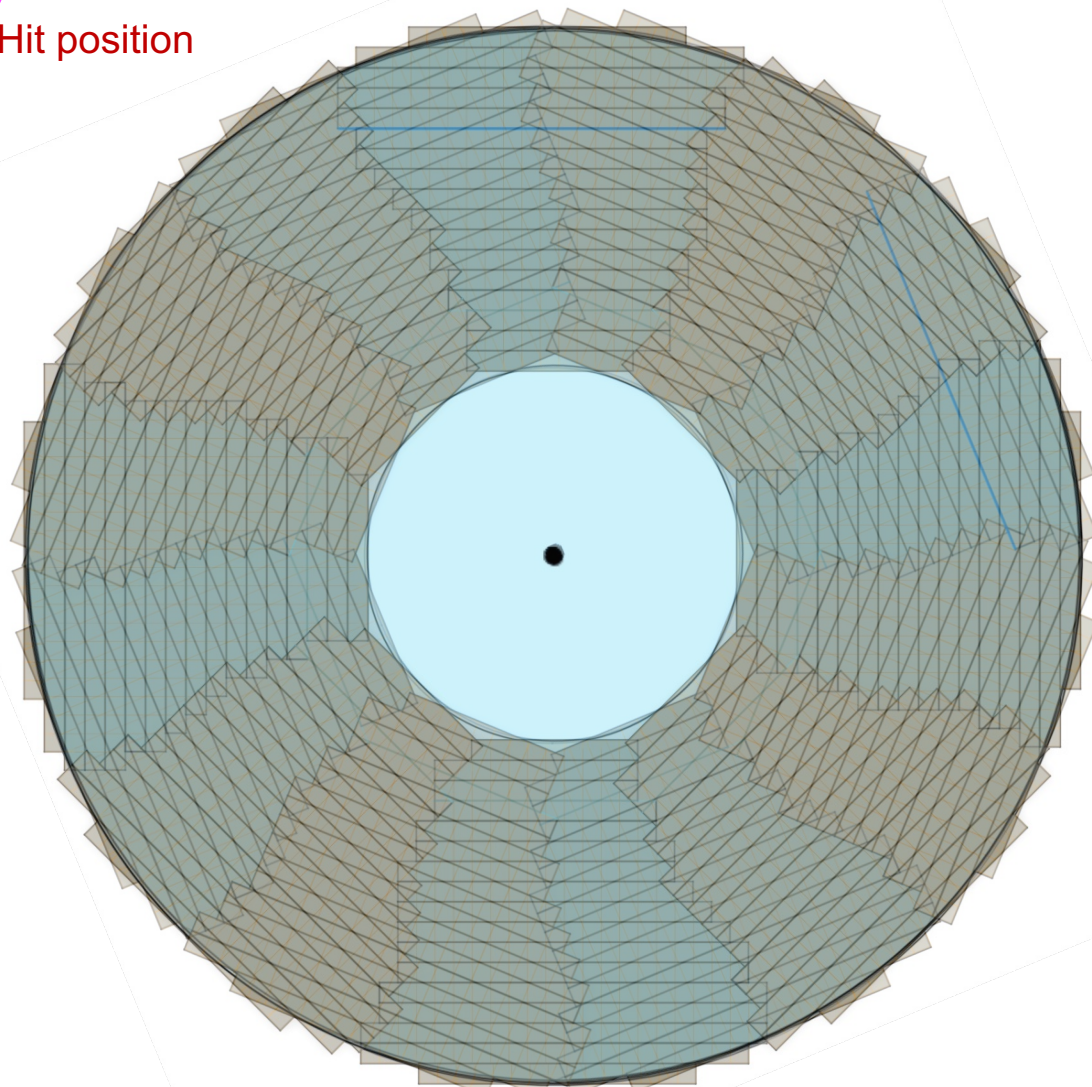
端盖正常半层



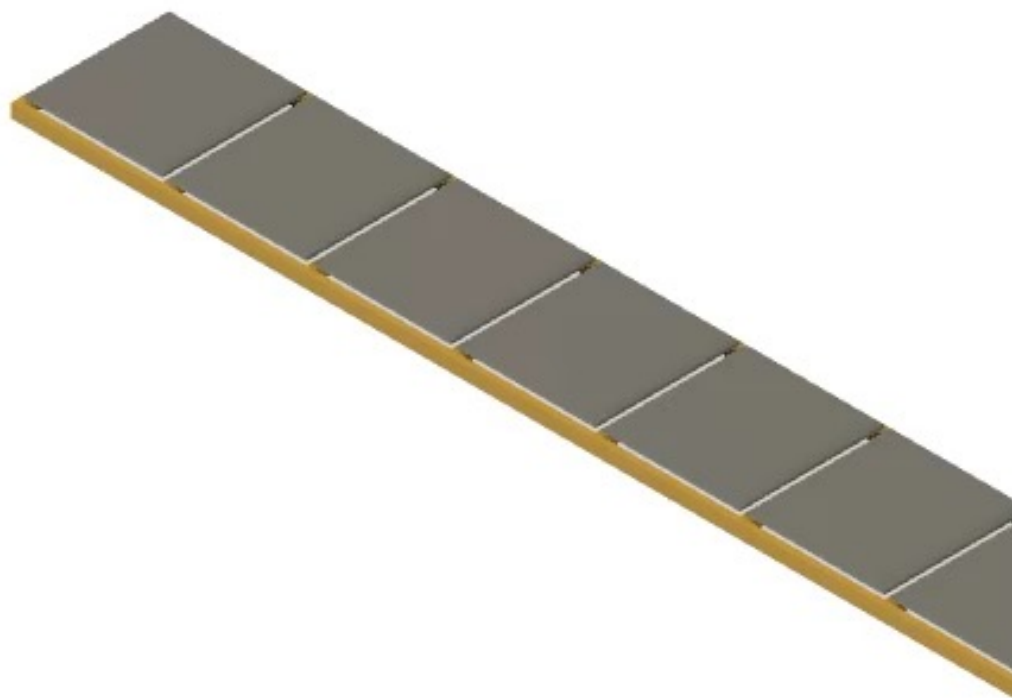
端盖22.5°半层



Hit position



端盖一层



端盖探测元件统计

	Module Types	Sensors	Sensor area	Overlap area Fraction
ITKE1	5	784*2=1568	0.76 m ²	0.138
ITKE2	7	1584*2=3168	1.53 m ²	0.105
ITKE3	15	4784*2=9568	4.62 m ²	0.07
ITKE4	12	4208*2=8416	4.06 m ²	0.029
Total	18	22720	10.97 m ²	

芯片的总功耗（不包括其他电子学元件）： 21.9 KW (200 mW/cm²)

端盖的机械和散热设计和分析

CMOS Chip Parameters

	HVCMOS Pixels (Barrel)	CMOS Strips (Endcap)
Pixel Size/Strip Size	$34 \times 150 \mu\text{m}^2$	$20 \mu\text{m}$
Chip size	$\sim 2 \times 2 \text{ cm}^2$	$2.1 \times 2.3 \text{ cm}^2$ (active area: $2.05 \times 2.05 \text{ cm}^2$)
Array size/Strip number	512 rows $\times$ 128 columns	1,024
Spatial resolution	$\sigma_\phi \sim 8 \mu\text{m}$, $\sigma_z \sim 40 \mu\text{m}$	$\sigma_\phi \sim 4.2 \mu\text{m}$, $\sigma_r \sim 21 \mu\text{m}$
Timing resolution	$\sim 3\text{-}5 \text{ ns}$	$\sim 3\text{-}5 \text{ ns}$
Data size per hit	42 bit (14b BXID*, 7b+9b address, 6b TOT, 5b fine TDC, 1 polarity*)	32 bits (10b BXID, 10b address, 6b TOT, other 6 bits)
Event rate / chip	??? (background?) up to 1.28 Gbps	Maximum $\sim 0.25 \text{ Gbps}$ (pair production)
LV / HV	1.2V / $>50 \text{ V}$	1.5V / $>50 \text{ V}$

* To be reduced